Ordering number : ENN3462B

N-Channel Silicon MOSFET





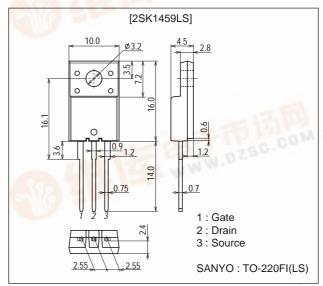
# **Ultrahigh-Speed Switching Applications**

### **Features**

- · Low ON-resistance.
- · Ultrahigh-speed switching.
- · Micaless package facilitating mounting.

### **Package Dimensions**

unit : mm 2078C



## **Specifications**

Absolute Maximum Ratings at Ta=25°C

| Parameter                   | Symbol | Conditions             | Ratings     | Unit |
|-----------------------------|--------|------------------------|-------------|------|
| Drain-to-Source Voltage     | VDSS   |                        | 900         | V    |
| Gate-to-Source Voltage      | VGSS   |                        | ±30         | ٧    |
| Drain Current (DC)          | ID     | a sales l              | 2.5         | Α    |
| Drain Current (Pulse)       | IDP    | PW≤10μs, duty cycle≤1% | 5           | Α    |
| Allowable Power Dissipation | D-     |                        | 2.0         | W    |
|                             | PD     | Tc=25°C                | 30          | W    |
| Channel Temperature         | Tch    | L'al Car               | 150         | °C   |
| Storage Temperature         | Tstg   | C.Com                  | -55 to +150 | °C   |

#### Electrical Characteristics at Ta=25°C

| Parameter                         | Symbol   | Conditions                                |     | Ratings |      |      |
|-----------------------------------|----------|---|-----|---------|------|------|
|                                   |          |   | min | typ     | max  | Unit |
| Drain-to-Source Breakdown Voltage | V(BR)DSS | ID=1mA, VGS=0                             | 900 |         |      | V    |
| Zero-Gate Voltage Drain Current   | IDSS     | V <sub>DS</sub> =900V, V <sub>GS</sub> =0 |     |         | 1.0  | mA   |
| Gate-to-Source Leakage Current    | IGSS     | V <sub>GS</sub> =±30V, V <sub>DS</sub> =0 |     | 100     | ±100 | nA   |
| Cutoff Voltage                    | VGS(off) | V <sub>DS</sub> =10V, I <sub>D</sub> =1mA | 2.0 |         | 3.0  | V    |
| Forward Transfer Admittance       | yfs      | Vps=20V, Ip=1.5A                          | 0.8 | 1.5     |      | S    |

Marking: K1459 Continued on next page.

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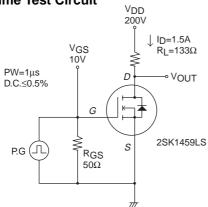
# 2SK1459LS

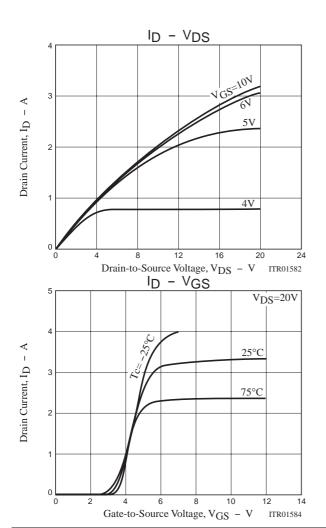
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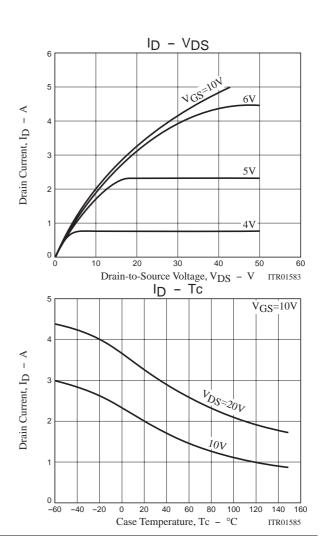
| Parameter                                  | Symbol              | Conditions  | Ratings |     |     | Unit  |
|--|---------------------|---|---------|-----|-----|-------|
|  |                     |   | min     | typ | max | Offic |
| Static Drain-to-Source On-State Resistance | RDS(on)             | ID=1.5A, VGS=10V  |         | 4.7 | 60  | Ω     |
| Input Capacitance                          | Ciss                | V <sub>DS</sub> =20V, f=1MHz  |         | 350 |     | pF    |
| Output Capacitance                         | Coss                | V <sub>DS</sub> =20V, f=1MHz  |         | 150 |     | pF    |
| Reverse Transfer Capacitance               | Crss                | V <sub>DS</sub> =20V, f=1MHz  |         | 100 |     | pF    |
| Turn-ON Delay Time                         | t <sub>d</sub> (on) | I <sub>D</sub> =1.5A, V <sub>GS</sub> =10V, V <sub>DD</sub> =200V, R <sub>GS</sub> =50Ω |         | 15  |     | ns    |
| Rise Time                                  | t <sub>r</sub>      | I <sub>D</sub> =1.5A, V <sub>GS</sub> =10V, V <sub>DD</sub> =200V, R <sub>GS</sub> =50Ω |         | 25  |     | ns    |
| Turn-OFF Delay Time                        | td(off)             | I <sub>D</sub> =1.5A, V <sub>G</sub> S=10V, V <sub>DD</sub> =200V, R <sub>G</sub> S=50Ω |         | 120 |     | ns    |
| Fall Time                                  | tf                  | I <sub>D</sub> =1.5A, V <sub>G</sub> S=10V, V <sub>DD</sub> =200V, R <sub>G</sub> S=50Ω |         | 40  |     | ns    |
| Diode Forward Voltage                      | V <sub>SD</sub>     | I <sub>S</sub> =2.5A, V <sub>G</sub> S=0  |         |     | 1.8 | V     |

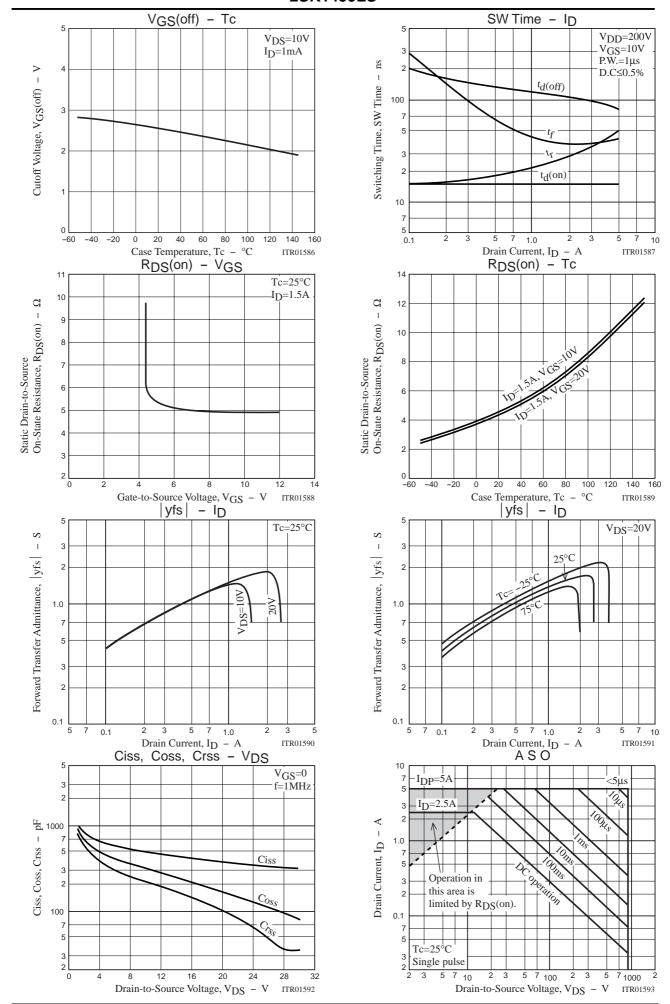
(Note) Be careful in handling the 2SK1459LS because it has no protection diode between gate and source.



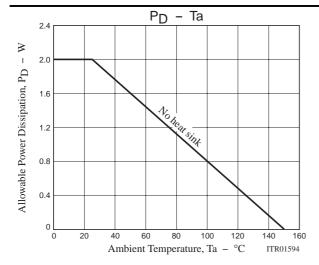


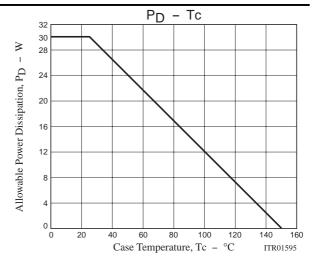






#### 2SK1459LS





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